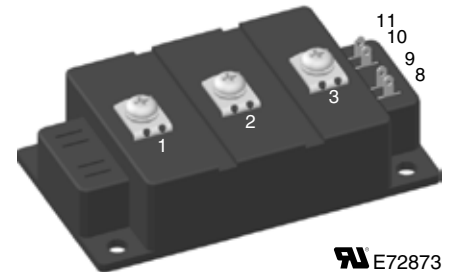
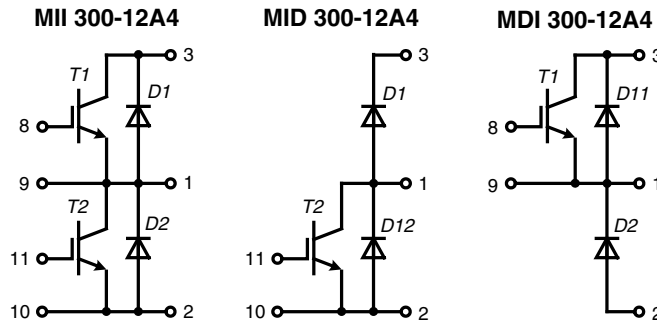


IGBT Modules

Short Circuit SOA Capability
 Square RBSOA

$I_{C25} = 330 \text{ A}$
 $V_{CES} = 1200 \text{ V}$
 $V_{CE(sat) \text{ typ.}} = 2.2 \text{ V}$



IGBTs T1 - T2		Maximum Ratings	
Symbol	Conditions		
V_{CES}	$T_{VJ} = 25^\circ\text{C to } 150^\circ\text{C}$	1200	V
V_{GES}		± 20	V
I_{C25}	$T_C = 25^\circ\text{C}$	330	A
I_{C80}	$T_C = 80^\circ\text{C}$	220	A
I_{CM}	$V_{GE} = \pm 15 \text{ V}; R_G = 3.3 \Omega; T_{VJ} = 125^\circ\text{C}$	400	A
V_{CEK}	RBSOA Clamped inductive load; $L = 100 \mu\text{H}$	V_{CES}	
t_{SC} (SCSOA)	$V_{CE} = V_{CES}; V_{GE} = \pm 15 \text{ V}; R_G = 3.3 \Omega$ $T_{VJ} = 125^\circ\text{C}; \text{non-repetitive}$	10	μs
P_{tot}	$T_C = 25^\circ\text{C}$	1380	W

Features

- NPT IGBT technology
- low switching losses
- switching frequency up to 30 kHz
- square RBSOA, no latch up
- high short circuit capability
- positive temperature coefficient for easy paralleling
- MOS input, voltage controlled
- ultra fast free wheeling diodes
- package with DCB ceramic base plate
- isolation voltage 4800 V
- UL registered E72873

Advantages

- space and weight savings
- reduced protection circuits

Applications

- AC and DC motor control
- AC servo and robot drives
- power supplies
- welding inverters

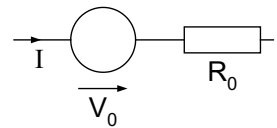
Symbol	Conditions	Characteristic Values				
		$(T_{VJ} = 25^\circ\text{C}, \text{ unless otherwise specified})$				
		min.	typ.	max.		
$V_{CE(sat)}$	$I_C = 200 \text{ A}; V_{GE} = 15 \text{ V}$		2.2	2.7	V	
$V_{GE(th)}$	$I_C = 8 \text{ mA}; V_{GE} = V_{CE}$	4.5		6.5	V	
I_{CES}	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}$ $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$			13	mA mA	
I_{GES}	$V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}$			± 800	nA	
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	Inductive load $V_{CE} = 600 \text{ V}; I_C = 200 \text{ A}$ $V_{GE} = \pm 15 \text{ V}; R_G = 3.3 \Omega$ $T_{VJ} = 125^\circ\text{C}$		100		ns	
				60		ns
				600		ns
				90		ns
				32		mJ
				29		mJ
C_{ies}	$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}; f = 1 \text{ MHz}$		13		nF	
C_{oes}			2		nF	
C_{res}			1		nF	
R_{thJC} R_{thJH}	(per IGBT) with heatsink compound		0.18	0.09	K/W K/W	

Free wheeling diodes D1 - D2 / D11 - D12

Symbol	Conditions	Maximum Ratings			
I_{F25}	$T_C = 25^\circ\text{C}$	450	A		
I_{F80}	$T_C = 80^\circ\text{C}$	280	A		
Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
V_F	$I_F = 300\text{ A}; V_{GE} = 0\text{ V};$ $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		2.2 1.7	2.5	V V
I_{RM} t_{rr}	$I_F = 200\text{ A}; di_F/dt = -1800\text{ A}/\mu\text{s};$ $V_R = 600\text{ V}; V_{GE} = 0\text{ V};$ $T_{VJ} = 125^\circ\text{C}$		180 200		A ns
R_{thJC} R_{thJH}	(per IGBT) with heatsink compound		0.3	0.15	K/W K/W

Equivalent Circuits for Simulation

Conduction

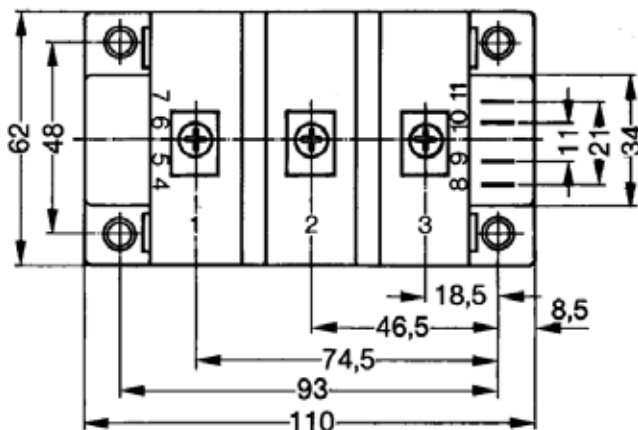
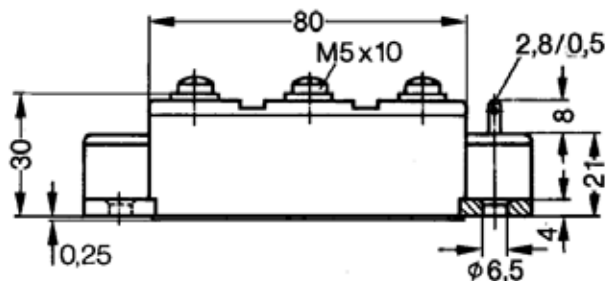


IGBT (typ. at $V_{GE} = 15\text{ V}; T_J = 125^\circ\text{C}$)
 $V_0 = 1.3\text{ V}; R_0 = 6.2\text{ m}\Omega$

Free wheeling diode (typ. at $T_J = 125^\circ\text{C}$)
 $V_0 = 1.3\text{ V}; R_0 = 2.4\text{ m}\Omega$

Module

Symbol	Conditions	Maximum Ratings			
T_{VJ}	operating	-40...+150	$^\circ\text{C}$		
T_{stg}		-40...+150	$^\circ\text{C}$		
V_{ISO}	$I_{ISOL} \leq 1\text{ mA}; 50/60\text{ Hz}$	4000	V~		
M_d	Mounting torque (module, M6) (terminal, M5)	2.25 - 2.75 2.5 - 3.7	Nm Nm		
Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
d_S	Creepage distance on surface	10			mm
d_A	Strike distance in air	9.6			mm
Weight			250		g



Dimensions in mm (1 mm = 0.0394")

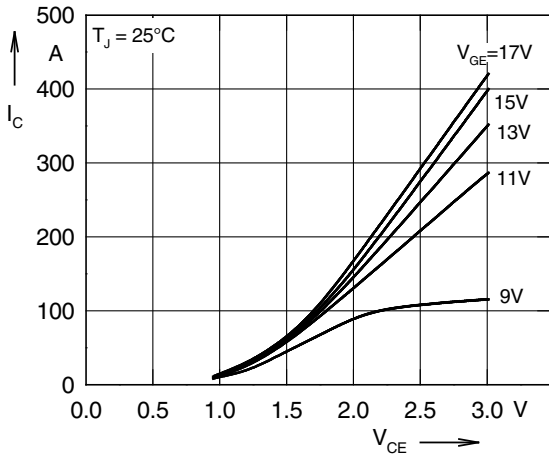


Fig. 1 Typ. output characteristics

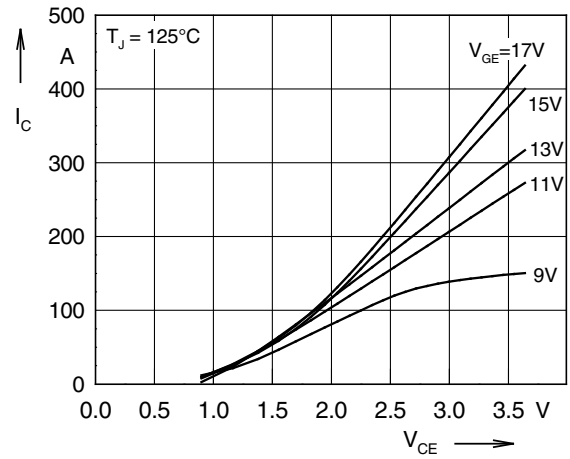


Fig. 2 Typ. output characteristics

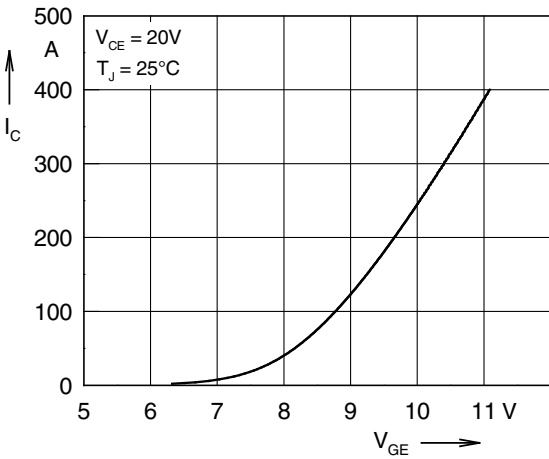


Fig. 3 Typ. transfer characteristics

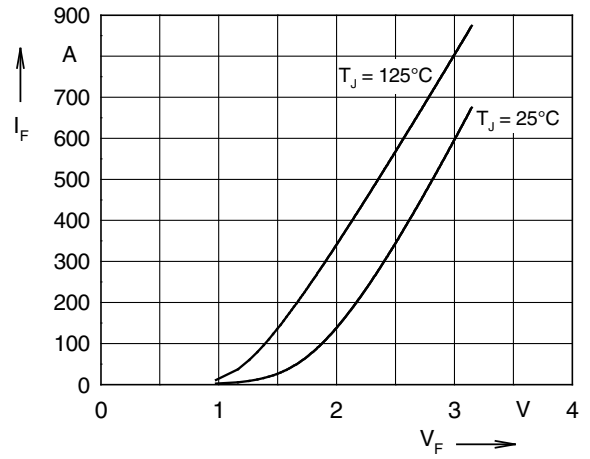


Fig. 4 Typ. forward characteristics of free wheeling diode

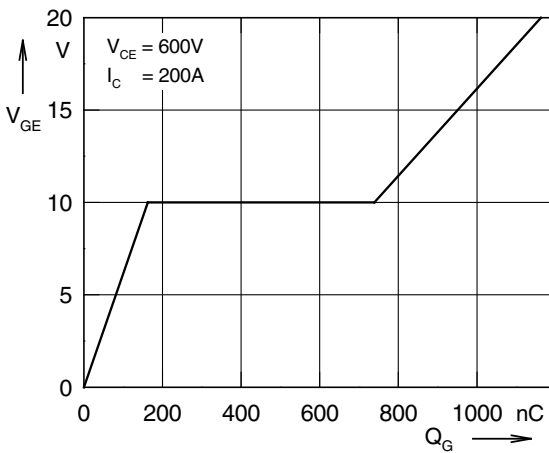


Fig. 5 Typ. turn on gate charge

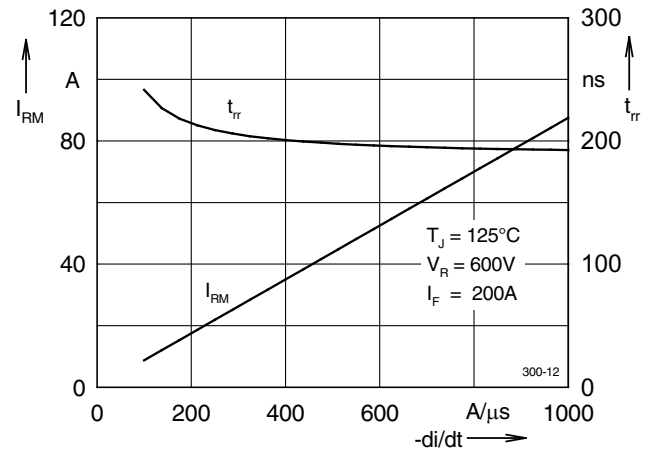


Fig. 6 Typ. turn off characteristics of free wheeling diode

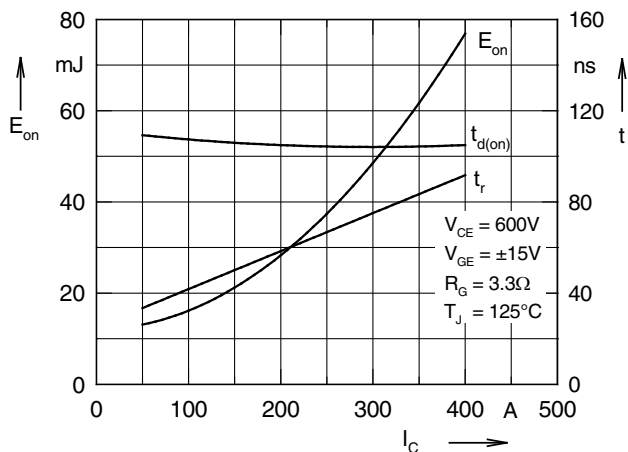


Fig. 7 Typ. turn on energy and switching

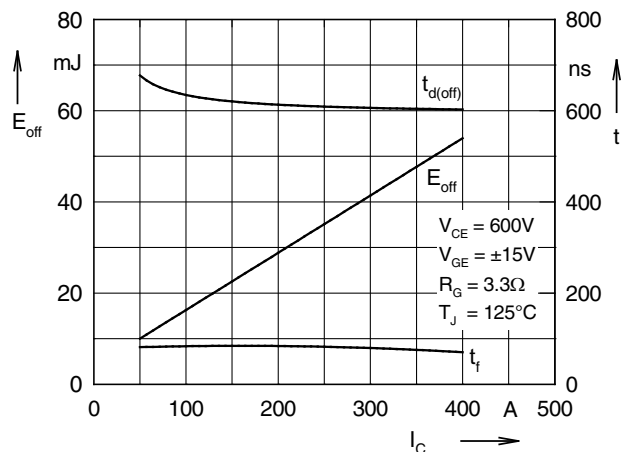


Fig. 8 Typ. turn off energy and switching times versus collector current

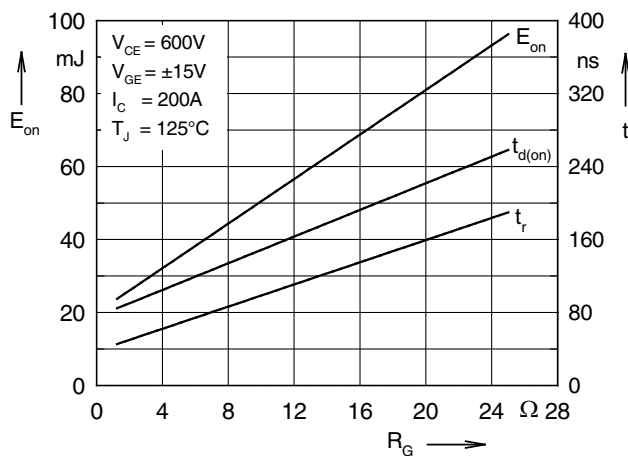


Fig. 9 Typ. turn on energy and switching times versus gate resistor

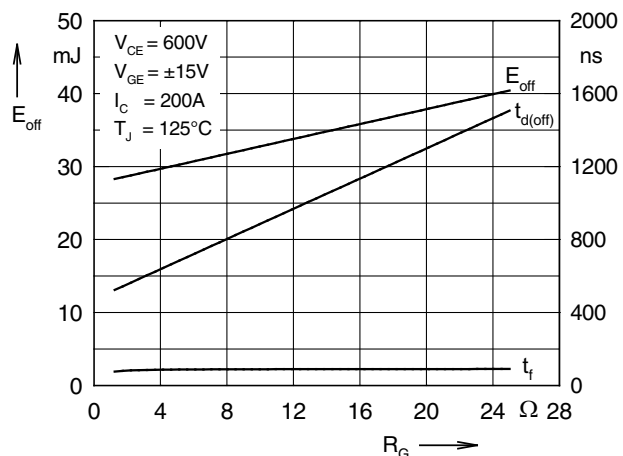


Fig. 10 Typ. turn off energy and switching times versus gate resistor

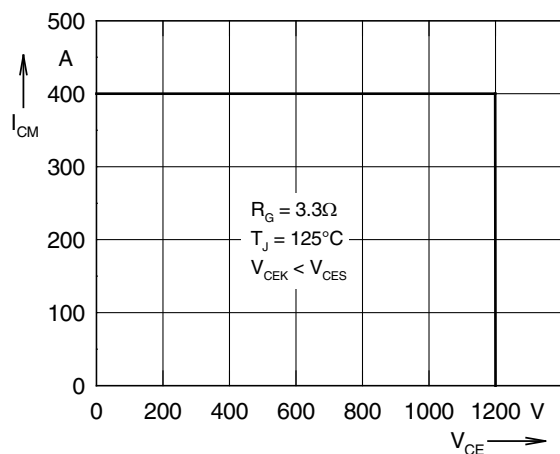


Fig. 11 Reverse biased safe operating area RBSOA

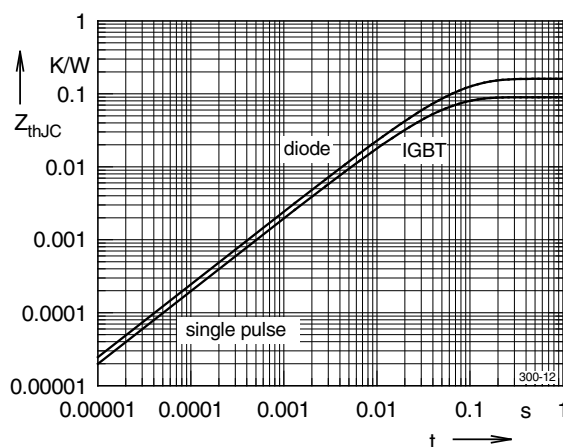


Fig. 12 Typ. transient thermal impedance

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